

650V 10A 0.75Ω N-ch Power MOSFET

Description

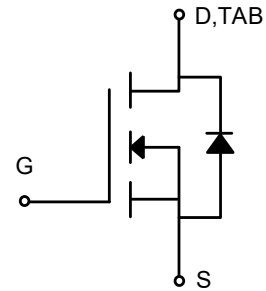
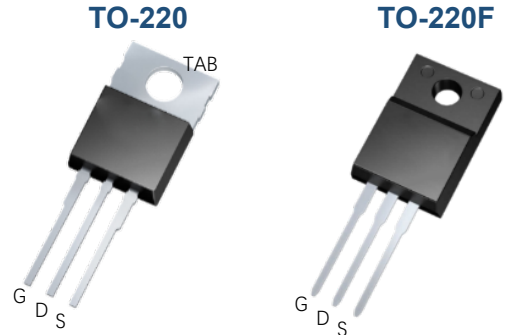
WMOS™ D1 is Wayon's 1st generation VDMOS family that is dramatic reduction in on-resistance and ultra-low gate charge for applications requiring high power density and high efficiency. And it is very robust and RoHS compliant.

Features

- $V_{DS}=700V@T_{jmax}$
- $Typ.R_{DS(on)}=0.75\Omega@V_{GS}=10V$
- 100% avalanche tested
- Pb-free, Halogen free

Applications

- SMPS
- Charger
- DC-DC



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	WMK	WML	Unit
Drain-source voltage	V_{DS}	650		V
Gate-source voltage	V_{GS}	± 30		V
Continuous drain current	I_D	10		A
Pulsed drain current ¹	I_{DM}	40		A
Avalanche energy, single pulse ²	E_{AS}	500		mJ
Power dissipation	P_D	150	63	W
Derate above 25°C		1.2	0.5	W/°C
Operating junction temperature	T_j	-55~150		°C
Storage temperature	T_{stg}	-55~150		°C
Continuous diode forward current	I_S	10		A
Diode pulse current	I_{Spulse}	40		A

Thermal Characteristic

Thermal resistance, junction-to-case	$R_{\theta JC}$	0.83	1.98	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	30	62.5	°C/W

Electrical Characteristics of MOSFET

				Min.	Typ.	Max.	
Drain-source break down voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	$T_C=25^\circ C$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu A, V_{DS}=V_{GS}$	$T_J=25^\circ C$	2.0	2.9	4.0	V
Drain-source leakage current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$	$T_J=25^\circ C$	-	-	1	μA
		$V_{DS}=520V, V_{GS}=0V$	$T_J=125^\circ C$	-	-	100	μA
Gate-source leakage current,forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	$T_J=25^\circ C$	-	-	100	nA
Gate-source leakage current,reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	$T_J=25^\circ C$	-	-	-100	nA
Drain-source on-state resistance ³	$R_{DS(ON)}$	$V_{GS}=10V, I_D=5A$	$T_J=25^\circ C$	-	0.75	0.95	Ω
Transconductance ³	G_{fs}	$V_{DS}=20V$	$T_J=25^\circ C$	-	5.7	-	S

Dynamic Characteristics of MOSFET ($T_C=25^\circ C$)

				Min.	Typ.	Max.	
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V, V_{GS}=0V$		-	1570	-	pF
Output capacitance	C_{oss}			-	136	-	pF
Reverse transfer capacitance	C_{rss}			-	17.3	-	pF
Gate to source charge	Q_{gs}	$V_{DD}=320V$		-	9.9	-	nC
Gate to drain charge	Q_{gd}	$I_D=10A$		-	9.9	-	nC
Total gate charge	Q_g	$V_{GS}=0$ to 10V		-	34.5	-	nC

Switching Characteristics of MOSFET ($T_C=25^\circ C$)

				Min.	Typ.	Max.	
Turn-on delay time	t_{don}	$V_{DS}=320V, I_D=10A,$ $R_C=25\Omega, V_{GS}=0$ to 10V		-	21.2	-	ns
Rise time	t_r			-	38	-	ns
Turn-off delay time	t_{doff}			-	114	-	ns
Fall time	t_f			-	33.2	-	ns

Characteristics of Body Diode ($T_C=25^\circ C$)

				Min.	Typ.	Max.	
Forward voltage	V_{SD}	$I_{SD}=10A, V_{GS}=0V$		-	0.85	1.4	V
Reverse recovery time	t_{rr}	$V_{DS}=320V, I_S=10A, V_{GS}=0V$ $di/dt=100A/\mu s$		-	427	-	ns
Reverse recovery current	I_{rr}			-	14	-	A
Recovery charge	Q_{rr}			-	3	-	μC

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$.
2. The EAS data shows Max. rating . The test condition is $V_{DD}=50V, V_{GS}=10V, L=10mH, I_{AS}=10A, T_C=25^\circ C$.
3. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

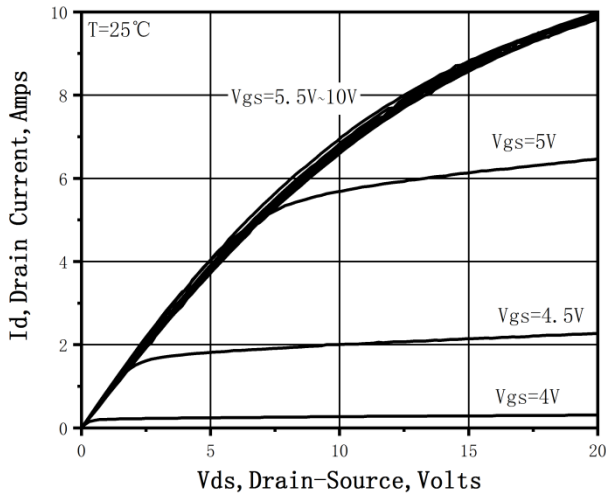


Figure 1. On-Region Characteristics

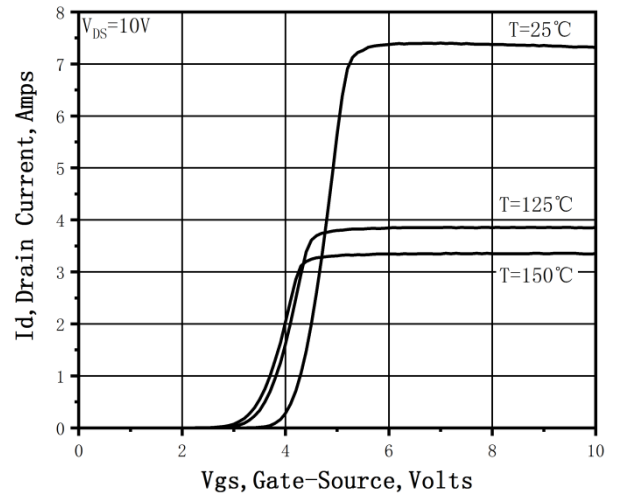


Figure 2. Transfer Characteristics

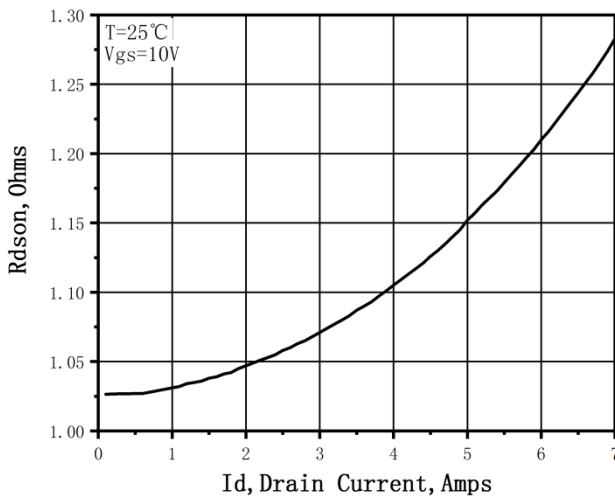


Figure 3. Static Drain-Source On Resistance

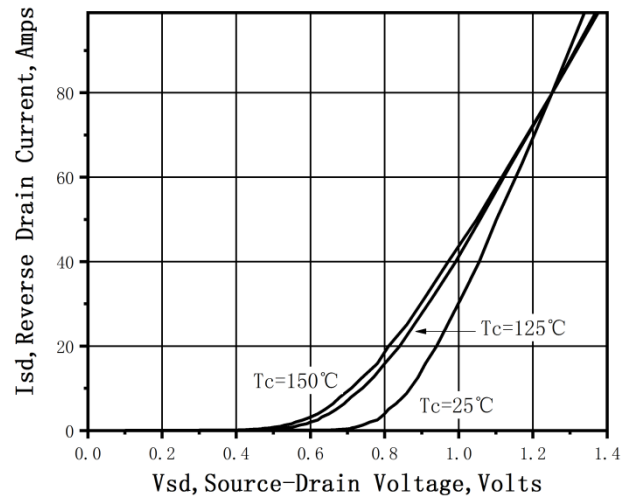


Figure 4. Typical Body Diode Transfer Characteristics

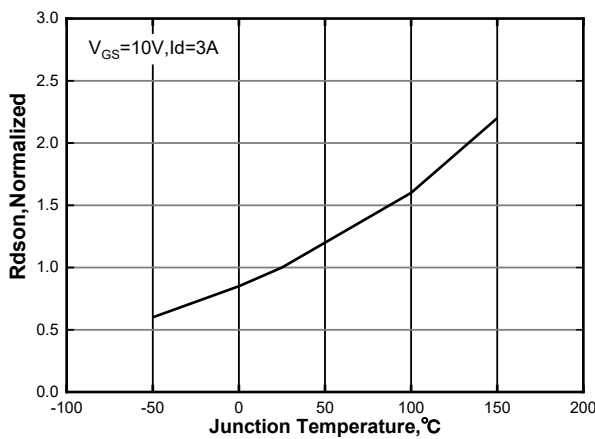


Figure 5. Normalized $R_{DS(on)}$ vs. Temperature

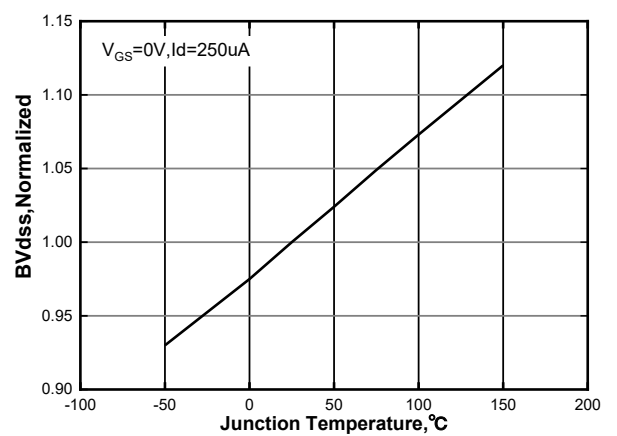


Figure 6. Normalized BV_{DSS} vs. Temperature

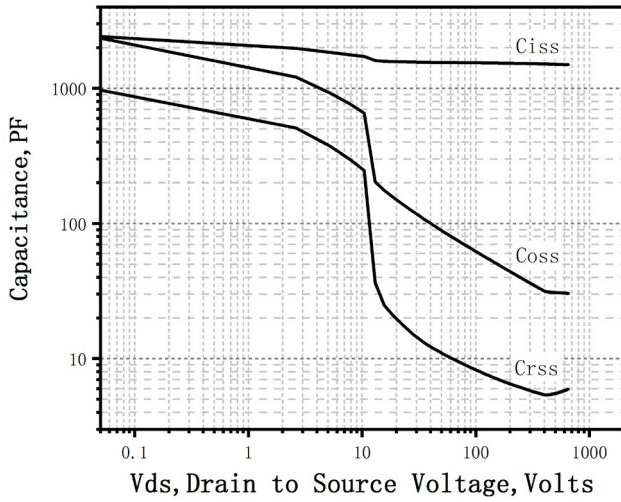


Figure 7. Capacitance Characteristics

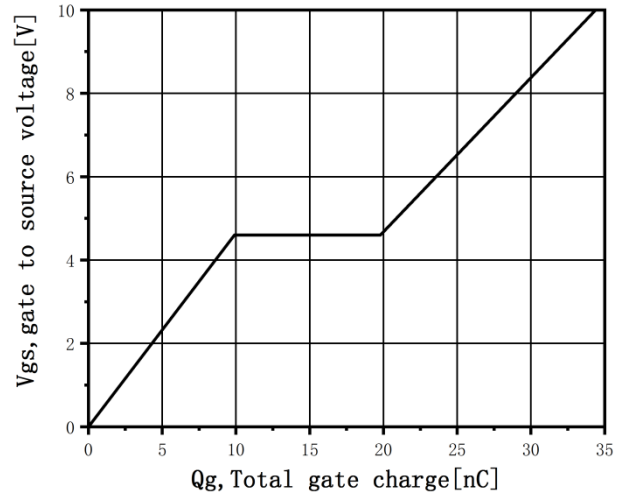


Figure 8. Gate Charge Characteristics

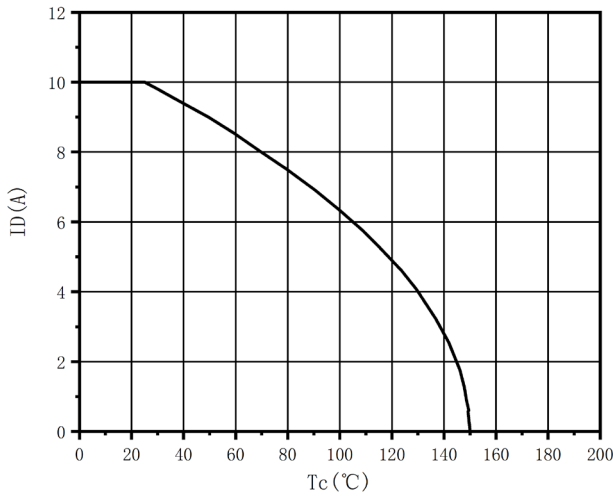


Figure 9. Continuous Drain Current Derating vs Case Temperature

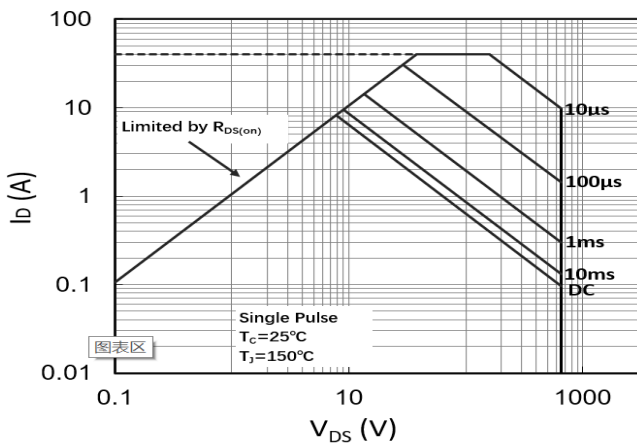


Figure 10. Maximum Safe Operating Area (TO-220F)

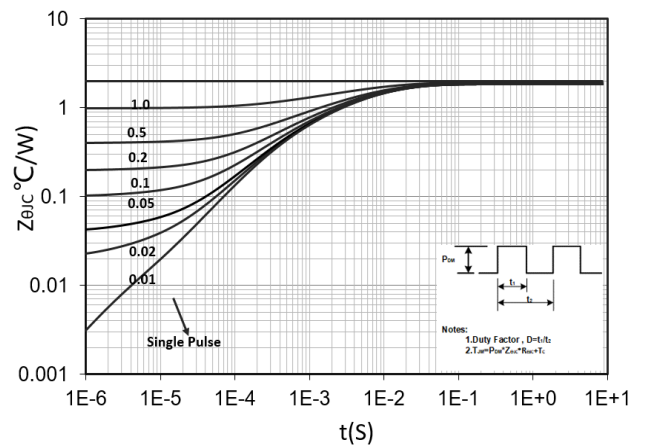


Figure 11. Transient Thermal Response Curve (TO-220F)

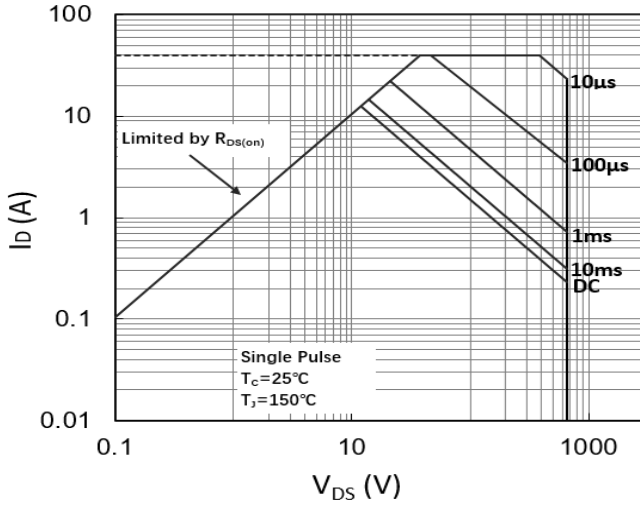


Figure 12. Maximum Safe Operating Area (TO-220)

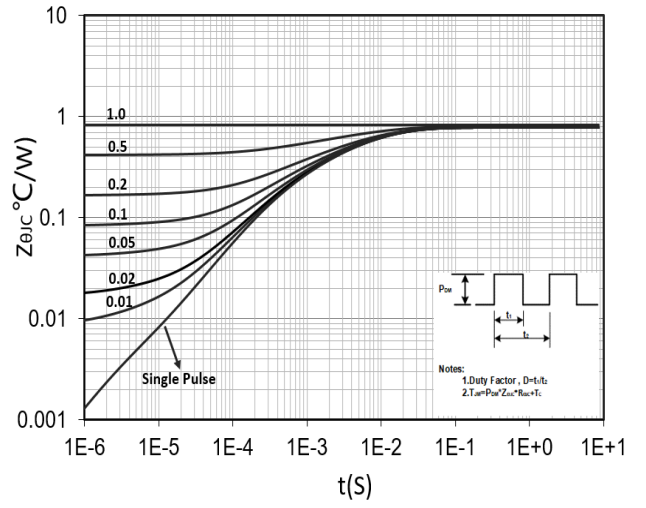
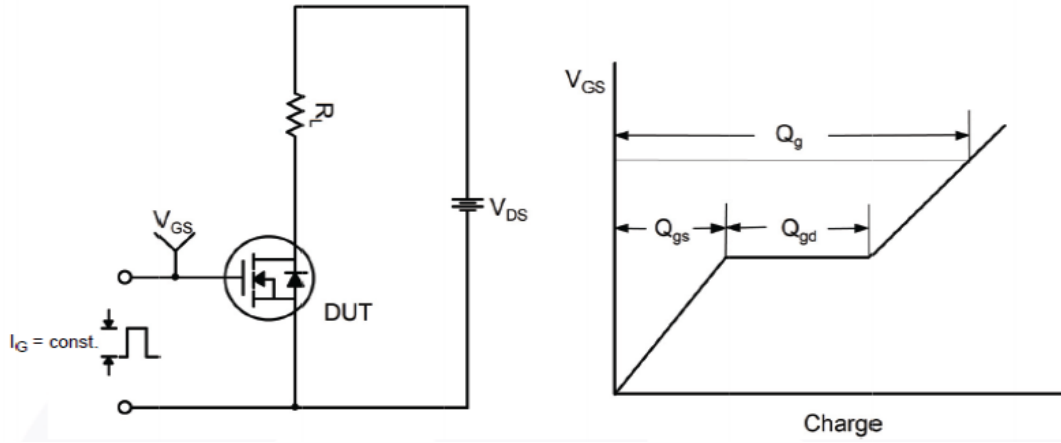
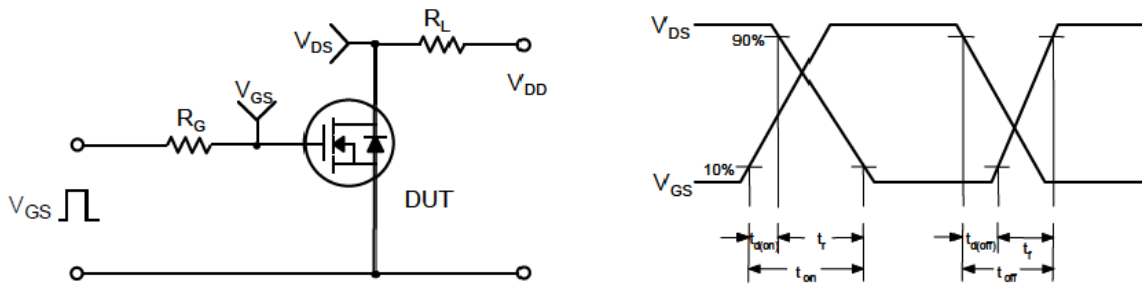


Figure 13. Transient Thermal Response Curve (TO-220)

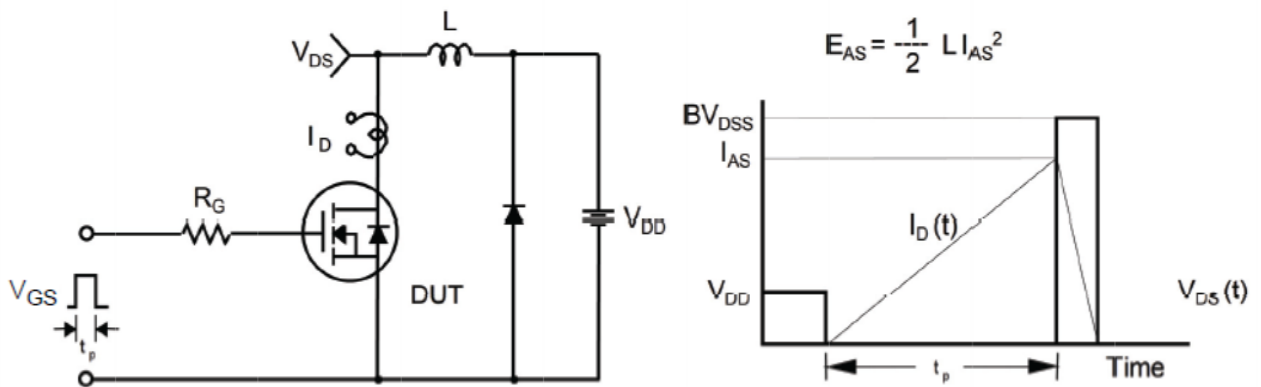
Gate Charge Test Circuit & Waveform



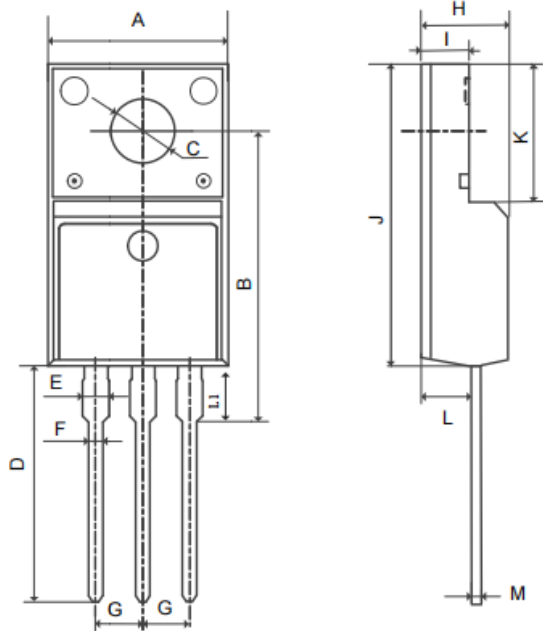
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



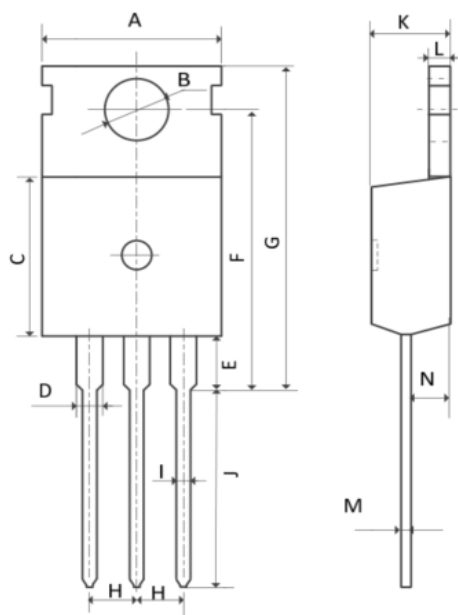
Mechanical Dimensions for TO-220F



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.10	16.10
C	3.03	3.38
D	12.64	13.28
E	1.18	1.58
F	0.70	0.95
G	2.54REF	
H	4.50	4.90
I	2.34	2.74
J	15.57	16.17
K	6.70REF	
L	2.56	2.96
M	0.40	0.65
L1	2.85	3.45

Mechanical Dimensions for TO-220



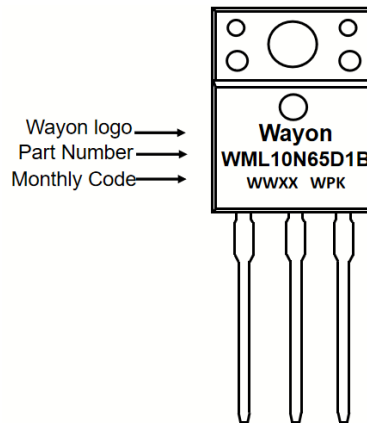
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.20
B	3.40	3.80
C	8.90	9.40
D	1.17	1.47
E	2.60	3.40
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Ordering Information

Part	Package	Marking	Packing method
WML10N65D1B	TO-220F	WML10N65D1B	Tube
WMK10N65D1B	TO-220	WMK10N65D1B	Tube

Marking Information



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